





#### 20V N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BVDSS	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
	0.99Ω @ V <sub>GS</sub> = 4.5V	760mA
20V	1.2Ω @ V <sub>GS</sub> = 2.5V	700mA
	2.4Ω @ V <sub>GS</sub> = 1.8V	500mA
	3.0Ω @ V <sub>GS</sub> = 1.5V	350mA

# **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- **Power Management Functions**
- Analog Switch

## **Features and Benefits**

- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V Max
- Low Input Capacitance
- Fast Switching Speed
- Ultra-Small Surface Mount Package 1mm x 0.6mm
- Low Package Profile, 0.5mm Maximum Package Height
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
  - For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

#### **Mechanical Data**

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.001 grams (Approximate)

X1-DFN1006-3

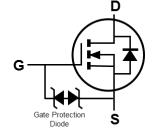




**Bottom View** 



Top View Pin Configuration



**Equivalent Circuit** 

### Ordering Information (Note 4)

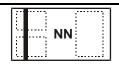
Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Tape Pitch (mm)	Quantity per Reel
DMN21D2UFB-7	NN	7	8	4	3,000
DMN21D2UFB-7B	NN	7	8	2	10,000

D

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

### **Marking Information**



NN = Product Type Marking Code

Top View Bar Denotes Gate and Source Side



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	lo	760 610	mA
Continuous Drain Current (Note 6) VGS = 4.5V	t<5s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	lo	850 700	mA
Maximum Continuous Body Diode Forward Current (Note 6)			Is	0.8	Α
Pulsed Drain Current (Note 7)			IDM	1.0	Α

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	0.38	W	
Total Power Dissipation (Note 5)	$T_A = +70^{\circ}C$	PD	0.25		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	325	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<5s	RθJA	244	C/VV	
Total Dawer Discinstion (Note 6)	T <sub>A</sub> = +25°C	D-	0.9	W	
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	PD	0.57		
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	р	141	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<5s	$R_{\theta JA}$	106	C/VV	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

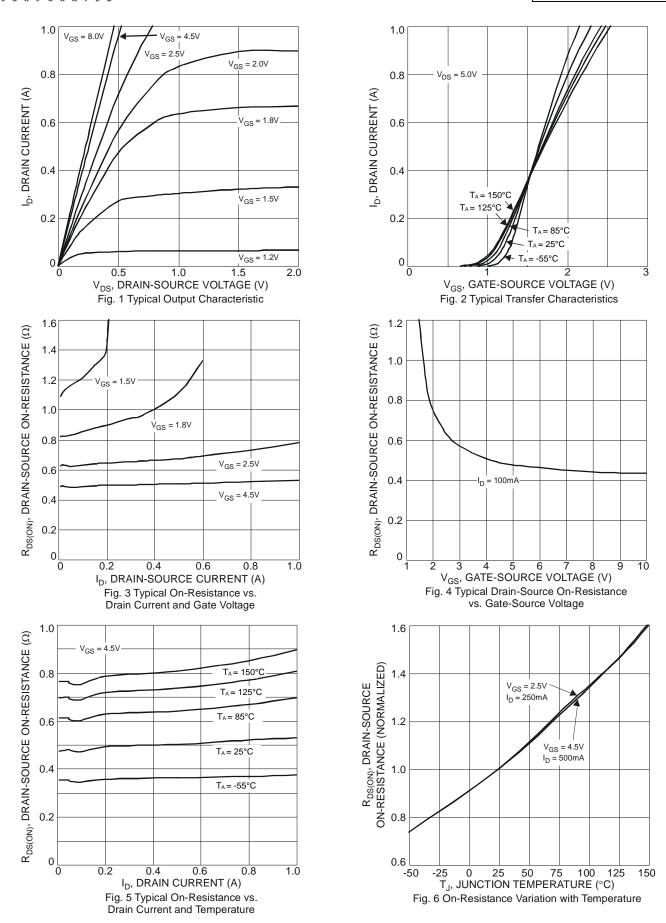
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage		20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current @Tc = +2	5°C IDSS	_	_	100	nA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	lgss	_	_	±1	μΑ	$V_{GS} = \pm 10V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	Vgs(TH)	0.4	_	1.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
		_	0.6	0.99		$V_{GS} = 4.5V, I_D = 100mA$	
Static Drain-Source On-Resistance	D	_	0.7	1.2		$V_{GS} = 2.5V, I_{D} = 50mA$	
Static Drain-Source On-Resistance	RDS(ON)	_	- 0.9 2.4	Ω	$V_{GS} = 1.8V, I_{D} = 20mA$		
		_	1.2	3.0		$V_{GS} = 1.5V, I_{D} = 10mA$	
Forward Transfer Admittance		180	_	_	ms	V <sub>DS</sub> = 10V, I <sub>D</sub> = 400mA	
Diode Forward Voltage		_	0.6	1.0	V	$V_{GS} = 0V, I_{S} = 150mA$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance		_	27.6	_	pF	101/11/	
Output Capacitance			4.0	_	pF	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, -f = 1.0MHz	
Reverse Transfer Capacitance		_	2.8	_	pF	1 - 1.01/11/12	
Total Gate Charge, VGS = 4.5V	Qg	_	0.41	_	nC		
Total Gate Charge, V <sub>GS</sub> = 10V		_	0.93	_	nC	\/ 40\/ I- 250m A	
Gate-Source Charge	Q <sub>gs</sub>	_	0.06	_	nC	$V_{DS} = 10V, I_{D} = 250mA$	
Gate-Drain Charge	$Q_{gd}$	_	0.06	_	nC	]	
Turn-On Delay Time	t <sub>D</sub> (ON)	_	3.5	_	ns	101/11/	
Turn-On Rise Time		_	4.2	_	ns	V <sub>DD</sub> = 10V, V <sub>GS</sub> = 4.5V,	
Turn-Off Delay Time		_	19.6	_	ns	$R_L = 47\Omega, R_g = 10\Omega,$ $R_D = 200 \text{mA}$	
Turn-Off Fall Time		_	9.8	_	ns	TID = ZUUTTA	

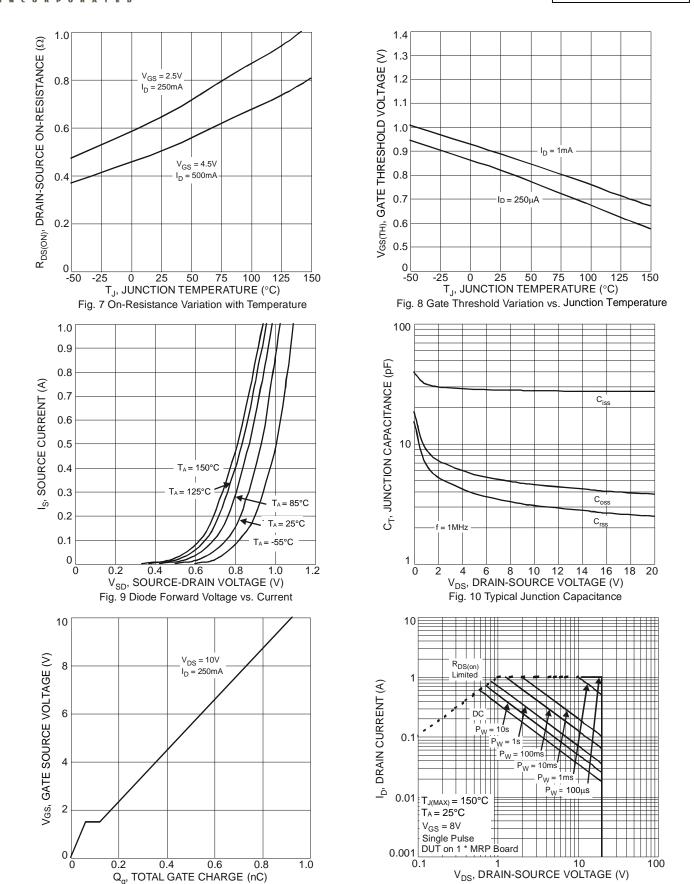
Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
- 7. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.







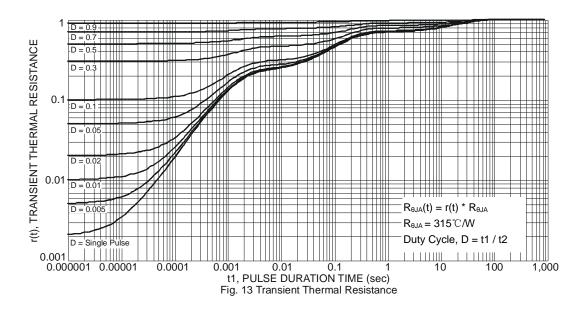


 $\mathbf{Q}_{\mathrm{g}}$ , TOTAL GATE CHARGE (nC)

Fig. 11 Gate Charge

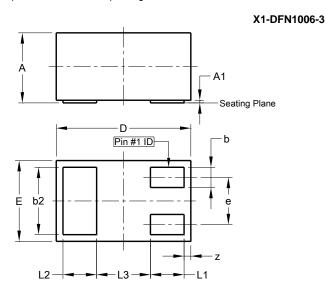
Fig. 12 SOA, Safe Operation Area





## **Package Outline Dimensions**

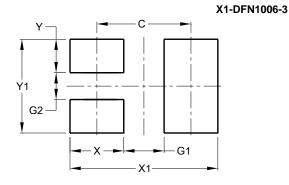
Please see http://www.diodes.com/package-outlines.html for the latest version.



X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
E	0.55	0.675	0.60		
е	-	-	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	-	-	0.40		
z	0.02	0.08	0.05		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)			
С	0.70			
G1	0.30			
G2	0.20			
Х	0.40			
X1	1.10			
Y	0.25			
Y1	0.70			



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